

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions,  
and listings, of claims in the application:

LISTING OF CLAIMS:

1-8. (canceled)

9. (previously presented) An ohmic electrode structure  
of a nitride semiconductor device having a nitride semiconductor,  
comprising:

a first metal film formed on the nitride semiconductor, and  
a second metal film formed on the first metal film,  
wherein the first metal film is made of at least one  
material selected from the group consisting of V, Mo, Ti, Nb, W,  
Fe, Hf, Re, Ta, and Zr, and

the second metal film is made of at least one material that  
is different from that of the first metal film and selected from  
the group consisting of V, Mo, Ti, Nb, W, Fe, Hf, Re, Ta, Zr, Pt,  
and Au,

excluding;

a combination of V as the first metal film and Pt or Au as  
the second metal film,

a combination of Ti as the first metal film and Mo, Pt or Au  
as the second metal film,

a combination of W as the first metal film and Pt or Au as the second metal film,

a combination of Hf as the first metal film and Au as the second metal film, and

a combination of Zr as the first metal film and Pt or Au as the second metal film.

10. (original) An electrode structure of a nitride semiconductor device according to claim 9, wherein:

the nitride semiconductor is a semiconductor containing GaN, AlN, InN, and their mixture as main components.

11. (previously presented) An electrode structure of a nitride semiconductor device according to claim 9, wherein:

a layer in which the material of the first metal film and Si are mixed is formed between the first metal film and the nitride semiconductor.

12. (previously presented) An ohmic electrode structure of a nitride semiconductor device having a nitride semiconductor, comprising:

a first metal film formed on the nitride semiconductor,  
a second metal film formed on the first metal film, and  
a third metal film formed on the second metal film,

wherein the first metal film is made of at least one material selected from the group consisting of V, Mo, Ti, Nb, W, Fe, Hf, Re, Ta, and Zr,

the second metal film is made of at least one material that is different from that of the first metal film and selected from the group consisting of V, Mo, Ti, Nb, W, Fe, Hf, Re, Ta, Zr, Pt, and Au, and

the third metal film is made of at least one material that is different from that of the second metal film and selected from the group consisting of V, Mo, Ti, Nb, W, Fe, Hf, Re, Ta, Zr, Pt, and Au,

excluding;

a combination of V as the first metal film and Pt or Au as the second metal film,

a combination of Ti as the first metal film and Mo, Pt or Au as the second metal film,

a combination of W as the first metal film and Pt or Au as the second metal film,

a combination of Hf as the first metal film and Au as the second metal film,

a combination of Zr as the first metal film and Pt or Au as the second metal film, and

a combination of Ti as the first metal film, Pt as the second metal film, and Au as the third metal film.

13. (original) An electrode structure of a nitride semiconductor device according to claim 12, wherein:

the nitride semiconductor is a semiconductor containing GaN, AlN, InN, and their mixture as main components.

14. (previously presented) An electrode structure of a nitride semiconductor device according to claim 12, wherein:

a layer in which the material of the first metal film and Si are mixed is formed between the first metal film and the nitride semiconductor.

15-16. (canceled)